

**AMENDMENTS TO THE SPECIFICATION:**

Please amend the Specification as follows.

**Please delete the eighteen paragraphs beginning on page 5, line 16 and ending on page 18, line 25.**

**Please insert the following paragraph on page 5, line 16 after “BRIEF SUMMARY OF THE INVENTION.”**

A semiconductor device according to an aspect of the present invention comprises: a semiconductor substrate of a first conductivity type; a convex semiconductor layer of the first conductivity type on the semiconductor substrate; a source region and a drain region of a second conductivity type in the convex semiconductor layer; a gate insulator on side surfaces of the convex semiconductor layer and a top surface of the convex semiconductor layer; a gate electrode on a portion of the gate insulator between the source region and the drain region; and a trench capacitor in the semiconductor substrate, the trench capacitor connected to one of the source and drain regions.